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June 2013

FJD5555

NPN Silicon Transistor

Features

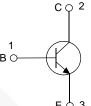
- · Fast Speed Switching
- Wide Safe Operating Area
- High Voltage Capability

Application

- Electronic Ballast
- · Switch Mode Power Supplies



1. Base 2. Collector 3. Emitter



Ordering Information

Part Number	Marking	Package	Packing Method	
FJD5555TM	J5555	D-PAK	Tape & Reel	

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at $T_A = 25^{\circ}\text{C}$ unless otherwise noted.

Symbol	Parameter	Value	Units
BV _{CBO}	Collector-Base Voltage	1050	V
BV _{CEO}	Collector-Emitter Voltage	400	V
BV _{EBO}	Emitter-Base Voltage	14	V
I _C	Collector Current (DC)	5	Α
I _{CP}	Collector Current (Pulse)	10	Α
Ι _Β	Base Current (DC)	2	Α
I _{BP}	Base Current (Pulse)	4	Α
T_J	Junction Temperature	150	°C
T _{STG}	Storage Junction Temperature Range	- 55 to +150	°C

Thermal Characteristics

Values are at $T_{\Lambda} = 25^{\circ}$ C unless otherwise noted.

Symbol	Parameter		Value	Units
P _D	Total Device Dissipation	T _A = 25°C	1.34	W
		$T_C = 25^{\circ}C$	100	W
$R_{\theta ja}^{(1)}$	Thermal Resistance, Junction to Ambient		95	°C/W
R _{θjc} ⁽²⁾	Thermal Resistance, Junction to Case		1.25	°C/W

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Notes

- 1. $R_{\theta ia}$ test board and fixture under natural convection; JESD51-3 recommended thermal test board.
- 2. $R_{\theta ic}$ test fixture under infinite cooling condition.

Electrical Characteristics(3)

Values are at $T_A = 25$ °C unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
BV _{CBO}	Collector-Base Breakdown Voltage	$I_C = 500 \mu A, I_E = 0$	1050			V
BV _{CEO}	Collector-Emitter Breakdown Voltage	$I_C = 5 \text{ mA}, I_B = 0$	400			V
BV _{EBO}	Emitter-Base Breakdown Voltage	$I_E = 500 \mu A, I_C = 0$	14			V
h _{FE}	DC Current Gain	$V_{CE} = 5 \text{ V}, I_{C} = 10 \text{ mA}$	10			
		$V_{CE} = 3 \text{ V}, I_{C} = 0.8 \text{ A}$	20		40	
V _{CE} (sat)	Collector-Emitter Saturation Voltage	$I_C = 1 \text{ A}, I_B = 0.2 \text{ A}$		0.17	0.50	V
		$I_C = 3.5 \text{ A}, I_B = 1.0 \text{ A}$			1.5	V
V _{BE} (sat)	Base-Emitter Saturation Voltage	$I_C = 3.5 \text{ A}, I_B = 1.0 \text{ A}$			1.2	V
C _{ob}	Output Capacitance	V _{CB} = 10 V, f = 1 MHz		45		pF
t _{ON}	Turn-On Time	$V_{CC} = 125 \text{ V}, I_{C} = 0.5 \text{ A},$			1.0	μs
t _{STG}	Storage Time	$I_{B1} = 45 \text{ mA}, I_{B2} = -0.5 \text{ A},$ $R_L = 250 \Omega$			1.2	μs
t _F	Fall Time			0.3		μs
t _{ON}	Turn-On Time	$V_{CC} = 250 \text{ V}, I_{C} = 2.5 \text{ A},$			2.0	μs
t _{STG}	Storage Time	$I_{B1} = 0.5 \text{ A}, I_{B2} = -1.0 \text{ A},$ $R_L = 100 \Omega$			2.5	μs
t _F	Fall Time				0.3	μs
EAS	Avalanche Energy	L = 2 mH	6			mJ

Note:

3. Pulse test: pulse width $\leq 300~\mu s,$ duty cycle $\leq 2\%.$

Typical Performance Characteristics

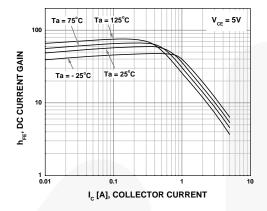


Figure 1. DC Current Gain

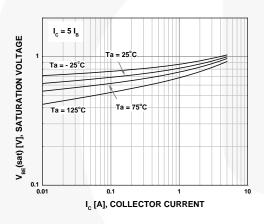


Figure 3. Saturation Voltage

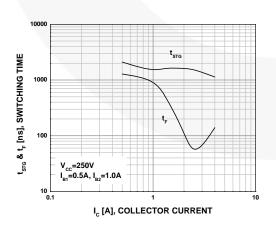


Figure 5. Resistive Load Switching

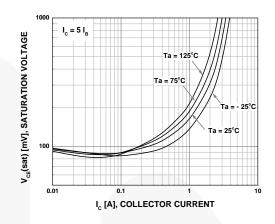


Figure 2. Saturation Voltage

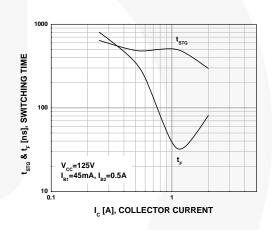


Figure 4. Resistive Load Switching

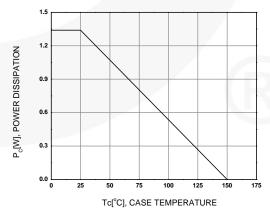


Figure 6. Power Derating

Typical Performance Characteristics (Continued)

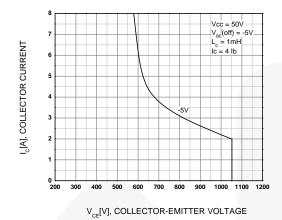


Figure 7. Reverse Bias Safe Operating

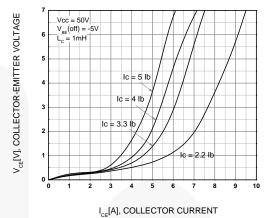
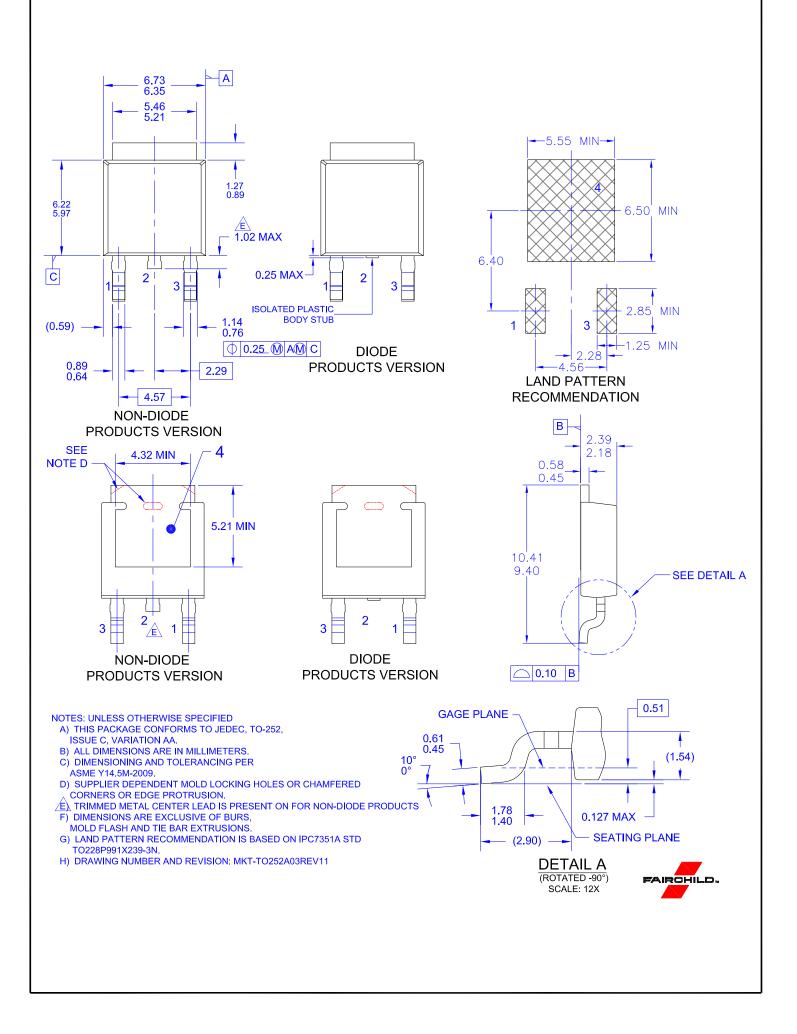


Figure 8. V_{CE} Saturation vs. h_{FE}



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